

General Description

The Alpha IGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The soft co-packaged diode is targeted for minimal losses in Welding machines, Solar Inverter and UPS applications.

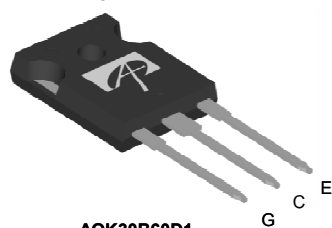
Product Summary

V_{CE}	600V
I_C ($T_C=100^\circ\text{C}$)	30A
$V_{CE(sat)}$ ($T_C=25^\circ\text{C}$)	1.85V

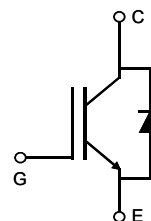


Top View

TO-247



AOK30B60D1



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	AOK30B60D1	Units
Collector-Emitter Voltage		V_{CE}	600	V
Gate-Emitter Voltage		V_{GE}	±20	V
V_{GE} Spike	500ns	V_{SPIKE}	24	V
Continuous Collector Current	$T_C=25^{\circ}\text{C}$	I_C	60	A
	$T_C=100^{\circ}\text{C}$		30	
Pulsed Collector Current, Limited by T_{Jmax}		I_{CM}	96	A
Turn off SOA, $V_{CE} \leq 600\text{V}$, Limited by T_{Jmax}		I_{LM}	96	A
Continuous Diode Forward Current	$T_C=25^{\circ}\text{C}$	I_F	30	A
	$T_C=100^{\circ}\text{C}$		15	
Diode Pulsed Current, Limited by T_{Jmax}		I_{FM}	96	A
Short circuit withstanding time $V_{GE} = 15\text{V}$, $V_{CE} \leq 400\text{V}$, Delay between short circuits $\geq 1.0\text{s}$, $T_C=25^{\circ}\text{C}$		t_{SC}	10	μs
Power Dissipation	$T_C=25^{\circ}\text{C}$	P_D	208	W
	$T_C=100^{\circ}\text{C}$		83	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

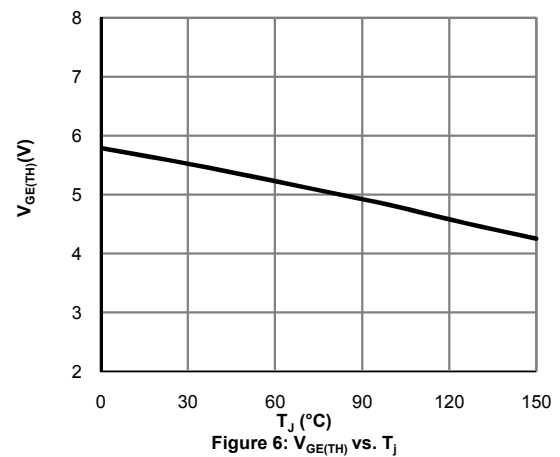
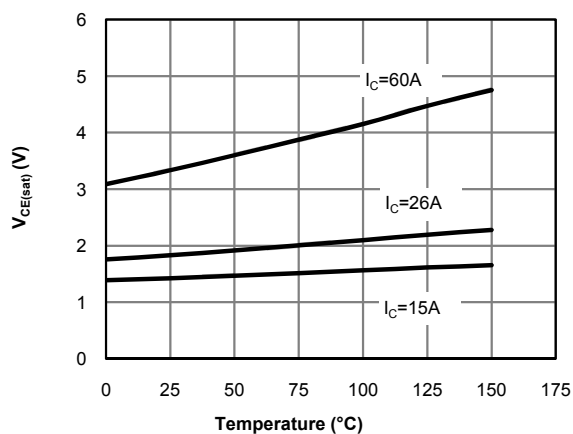
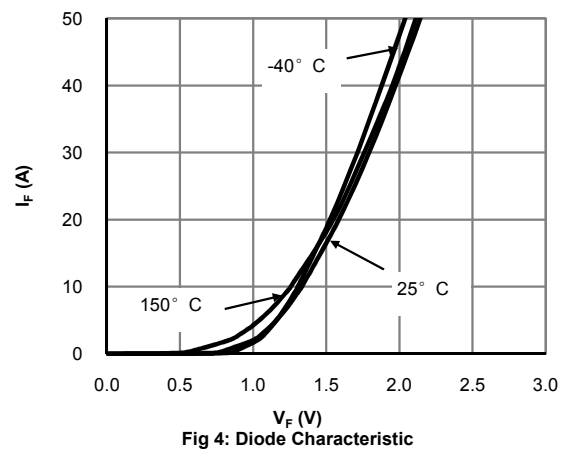
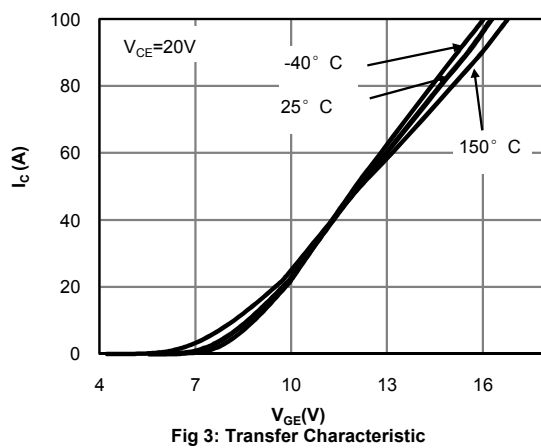
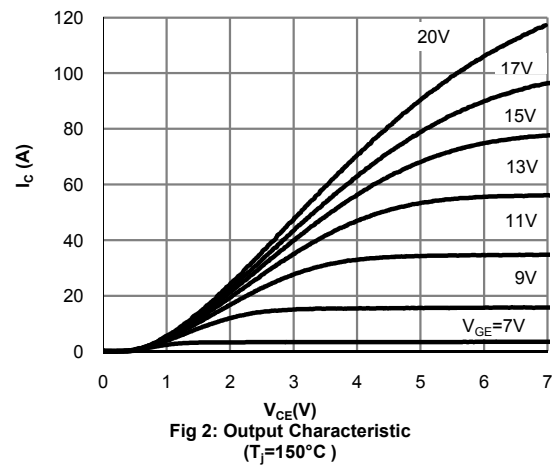
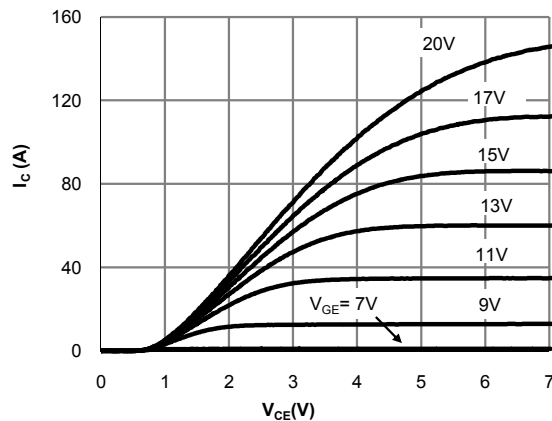
Parameter	Symbol	AOK30B60D1	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.6	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

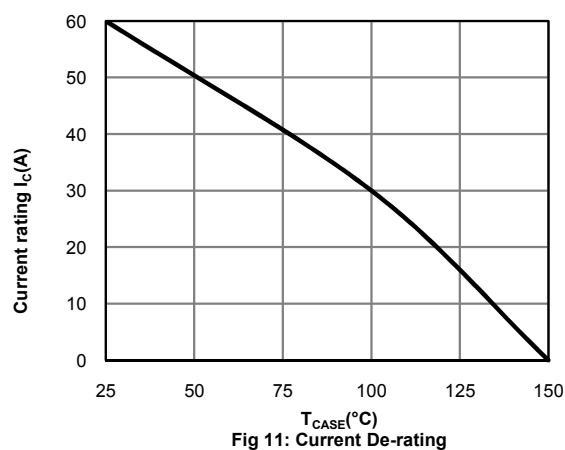
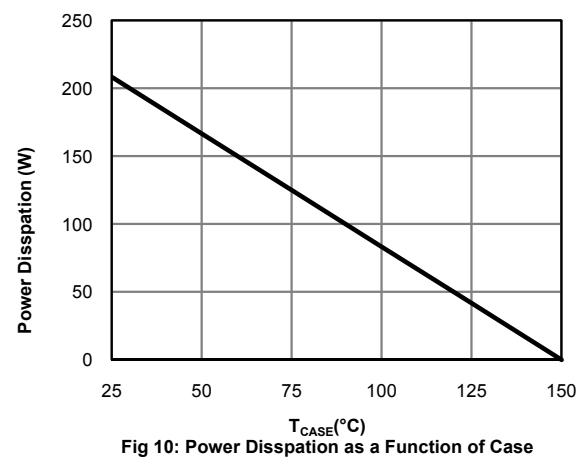
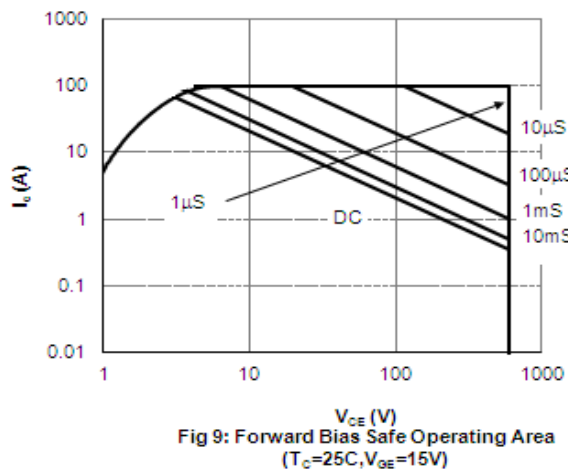
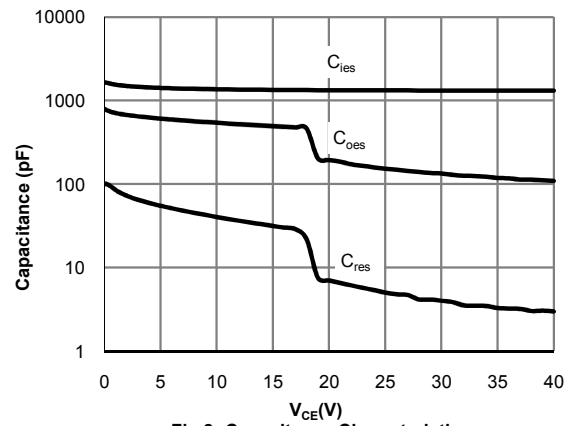
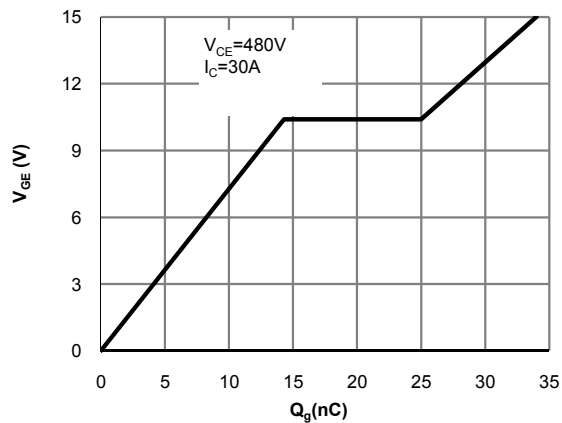
Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}$, $V_{GE}=0\text{V}$, $T_J=25^\circ\text{C}$	600	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}$, $I_C=26\text{A}$	$T_J=25^\circ\text{C}$	-	1.85	2.4
			$T_J=125^\circ\text{C}$	-	2.2	-
			$T_J=150^\circ\text{C}$	-	2.3	-
V_F	Diode Forward Voltage	$V_{GE}=0\text{V}$, $I_C=15\text{A}$	$T_J=25^\circ\text{C}$	-	1.47	2
			$T_J=125^\circ\text{C}$	-	1.44	-
			$T_J=150^\circ\text{C}$	-	1.42	-
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$	-	5.6	-	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=600\text{V}$, $V_{GE}=0\text{V}$	$T_J=25^\circ\text{C}$	-	-	10
			$T_J=125^\circ\text{C}$	-	-	400
			$T_J=150^\circ\text{C}$	-	-	2000
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0\text{V}$, $V_{GE}=\pm 20\text{V}$	-	-	± 100	nA
g_{FS}	Forward Transconductance	$V_{CE}=20\text{V}$, $I_C=30\text{A}$	-	13	-	S
DYNAMIC PARAMETERS						
C_{ies}	Input Capacitance	$V_{GE}=0\text{V}$, $V_{CE}=25\text{V}$, $f=1\text{MHz}$	-	1324	-	pF
C_{oes}	Output Capacitance		-	153	-	pF
C_{res}	Reverse Transfer Capacitance		-	5	-	pF
Q_g	Total Gate Charge	$V_{GE}=15\text{V}$, $V_{CE}=480\text{V}$, $I_C=30\text{A}$	-	34	-	nC
Q_{ge}	Gate to Emitter Charge		-	14.3	-	nC
Q_{gc}	Gate to Collector Charge		-	10.7	-	nC
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits $\geq 1.0\text{s}$	$V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_G=25\Omega$	-	96	-	A
R_g	Gate resistance	$f=1\text{MHz}$	-	1.3	-	Ω
SWITCHING PARAMETERS, (Load Inductive, $T_J=25^\circ\text{C}$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=25^\circ\text{C}$ $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=30\text{A}$, $R_G=10\Omega$, Parasitic Inductance=150nH	-	20	-	ns
t_r	Turn-On Rise Time		-	44	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	58	-	ns
t_f	Turn-Off Fall Time		-	16	-	ns
E_{on}	Turn-On Energy		-	1.1	-	mJ
E_{off}	Turn-Off Energy		-	0.24	-	mJ
E_{total}	Total Switching Energy		-	1.34	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=25^\circ\text{C}$	-	120	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=15\text{A}$, $dI/dt=200\text{A}/\mu\text{s}$, $V_{CE}=400\text{V}$	-	0.5	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	7	-	A
SWITCHING PARAMETERS, (Load Inductive, $T_J=150^\circ\text{C}$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=150^\circ\text{C}$ $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=30\text{A}$, $R_G=10\Omega$, Parasitic Inductance=150nH	-	21	-	ns
t_r	Turn-On Rise Time		-	45	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	70	-	ns
t_f	Turn-Off Fall Time		-	19	-	ns
E_{on}	Turn-On Energy		-	1.3	-	mJ
E_{off}	Turn-Off Energy		-	0.46	-	mJ
E_{total}	Total Switching Energy		-	1.76	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=150^\circ\text{C}$	-	206	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=15\text{A}$, $dI/dt=200\text{A}/\mu\text{s}$, $V_{CE}=400\text{V}$	-	0.9	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	9	-	A

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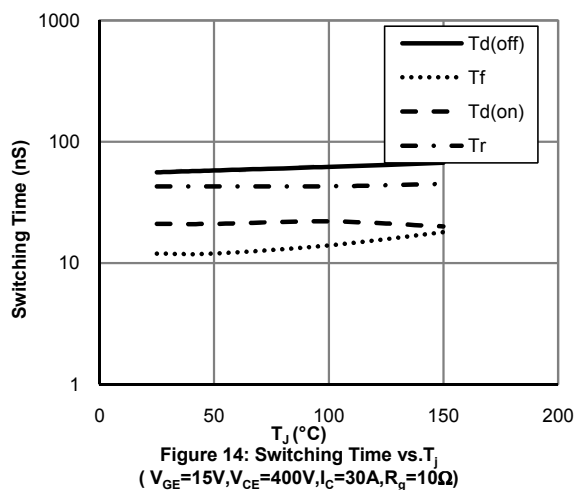
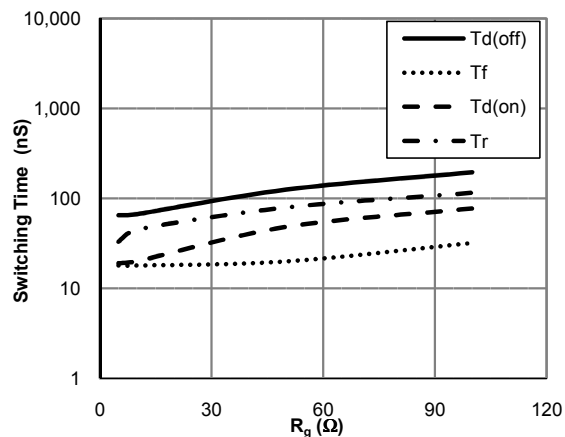
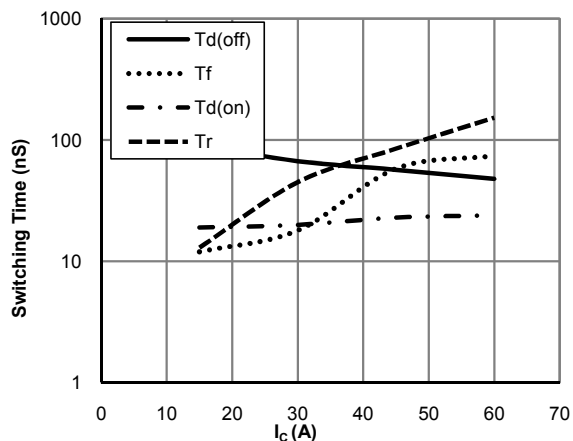
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



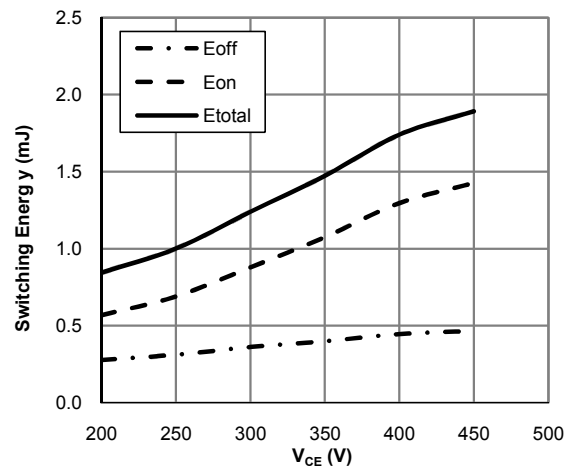
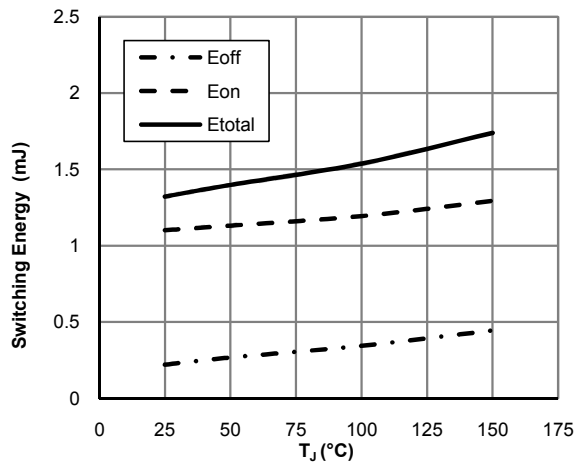
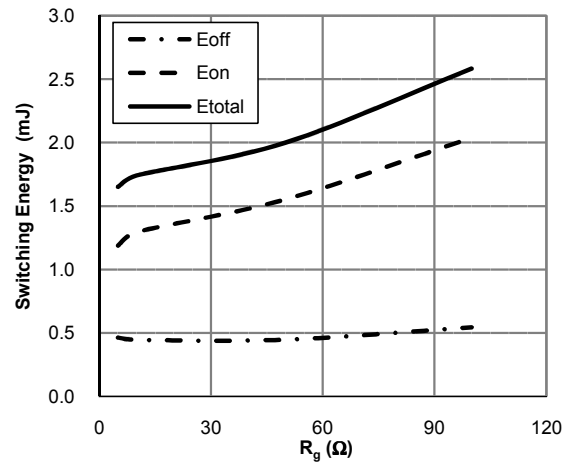
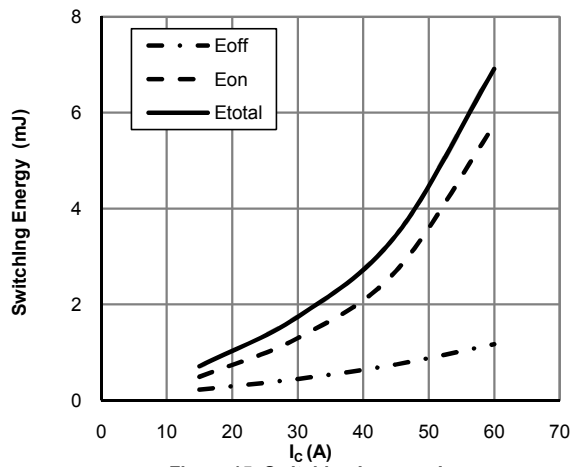
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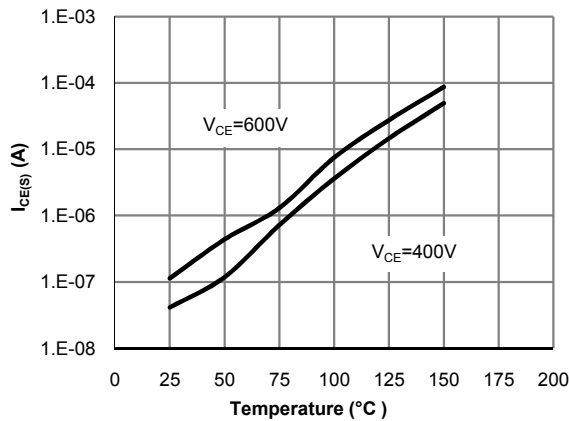


Fig 19: Diode Reverse Leakage Current vs. Junction Temperature

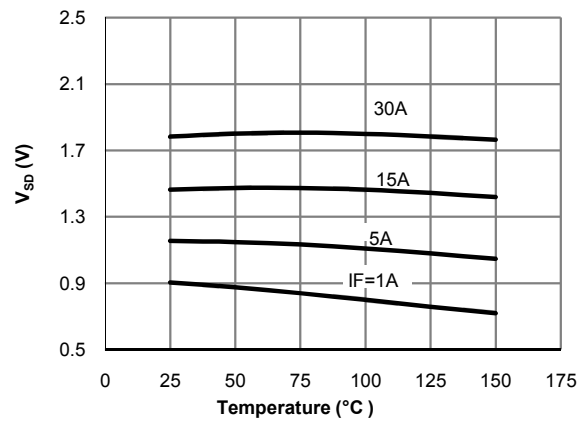


Fig 20: Diode Forward voltage vs. Junction Temperature

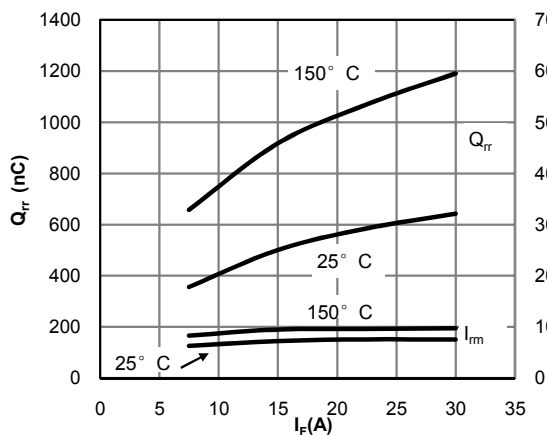


Fig 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

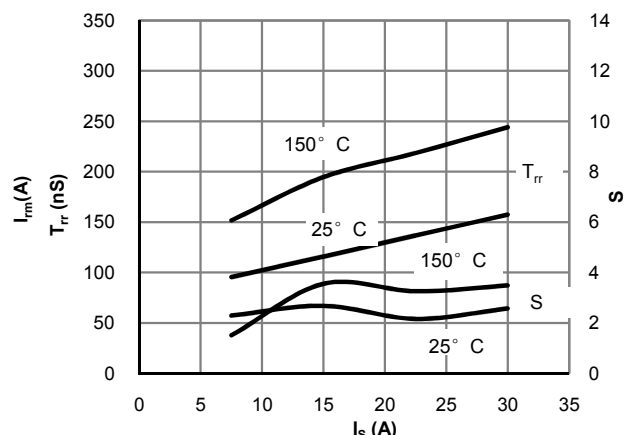


Fig 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

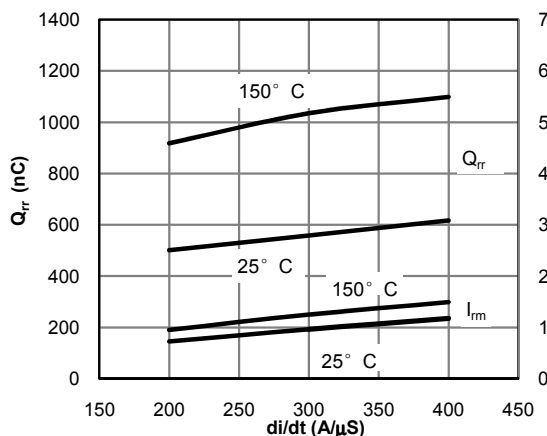


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

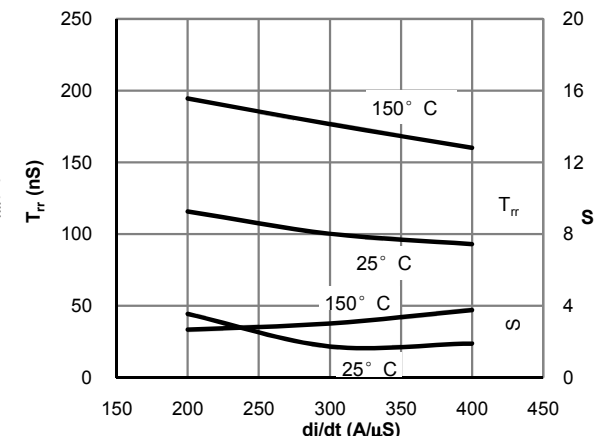


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

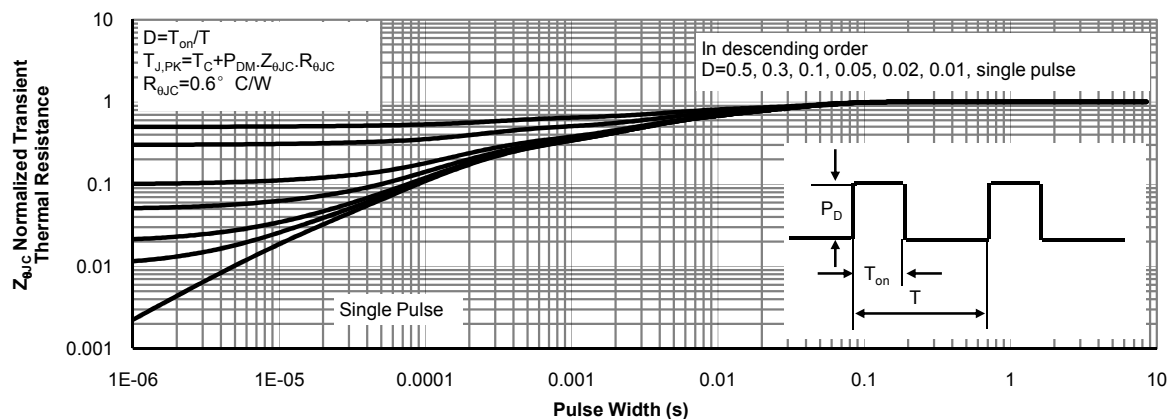


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

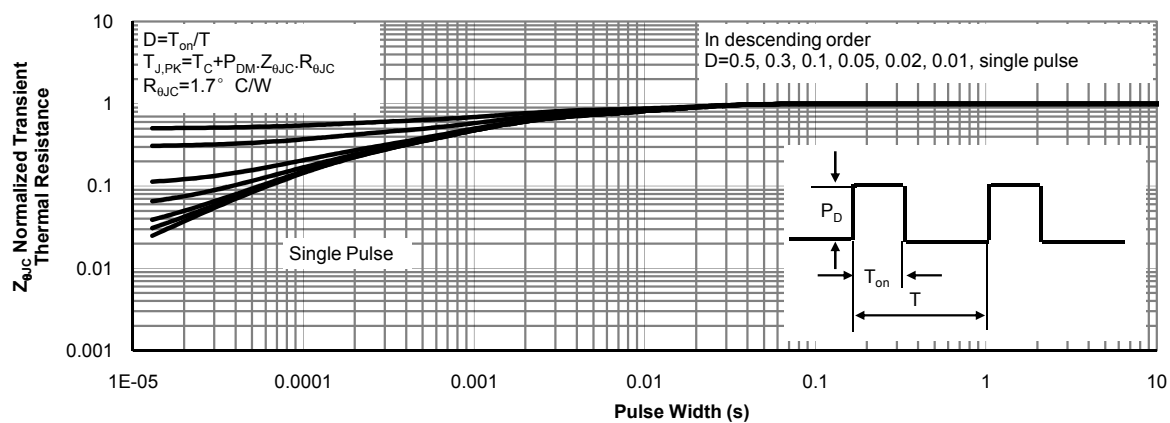
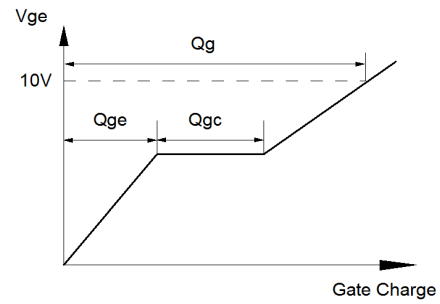
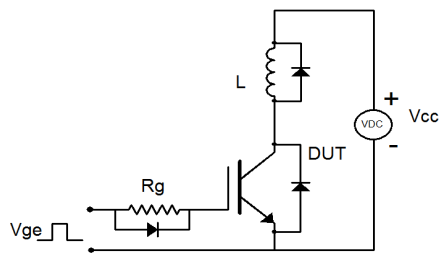
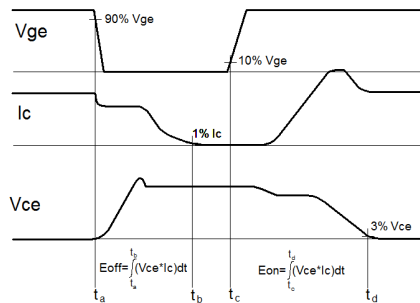
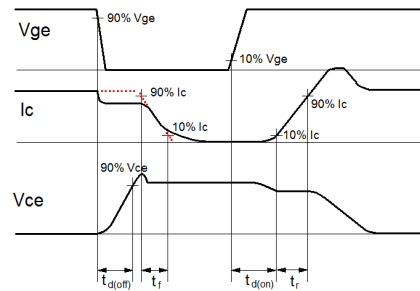
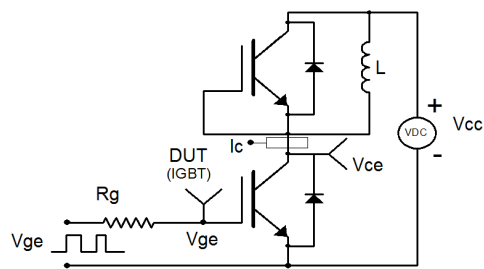


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

